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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	of	10

Complete if Known	
Application Number	09/853,233
Filing Date	May 11, 2001
First Named Inventor	Steven T. Harshfield
Art Unit	2823
Examiner Name	William D. Coleman
Attorney Docket Number	M4065.0743/P743

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	AB	2002/0168820 App.	11/2002	Kozicki	
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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Examiner Name	William D. Coleman
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Attorney Docket Number	M4065.0743/P473

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